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Tangring(10) **Pub. No.: US 2023/0231093 A1**(43) **Pub. Date: Jul. 20, 2023**(54) **OPTOELECTRONIC SEMICONDUCTOR CHIP**(52) **U.S. CL.**CPC *H01L 33/62* (2013.01); *H01L 25/0753* (2013.01)(71) Applicant: **ams-OSRAM International GmbH**,
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In an embodiment an optoelectronic semiconductor chip includes a semiconductor layer sequence including a first semiconductor layer, a second semiconductor layer, and an active layer arranged between the first semiconductor layer and the second semiconductor layer, a via having a plurality of recesses and a contact layer, wherein the first semiconductor layer has a first electrical contact region, wherein the second semiconductor layer has a second electrical contact region, wherein the via completely penetrates the first semiconductor layer and the active layer and is electrically connected to the second contact region, wherein the first contact region is arranged within the recesses of the via, and wherein the first contact region is divided into a plurality of partial regions, each partial region being arranged in one of the recesses and the partial regions being separated from each other.

